

2SA914

Silicon PNP Epitaxial Planar Type

AF Power Pre-amplifier

Complementary Pair with 2SC1953

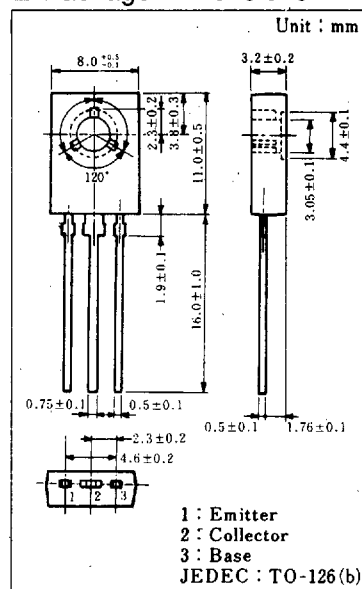
Features

- Good linearity of DC current gain (h_{FE})
- High collector-emitter voltage (V_{CE0})
- Low collector output capacitance (C_{ob})

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-150	V
Collector-emitter voltage	V_{CEO}	-150	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-100	mA
Collector current	I_C	-50	mA
Collector power dissipation	P_C	1.2	W
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

Package Dimensions

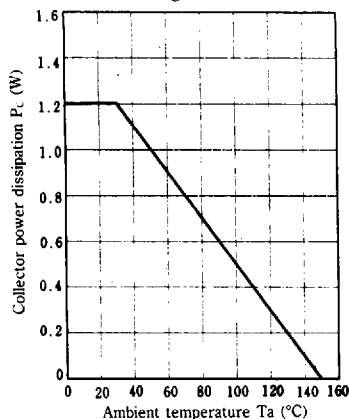
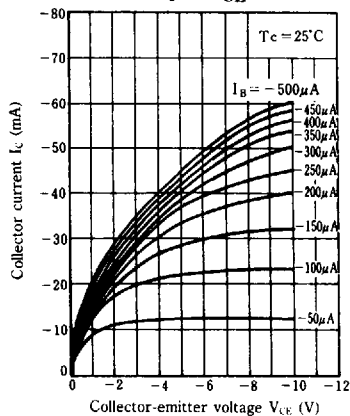
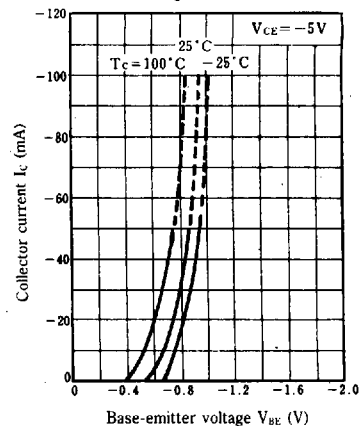
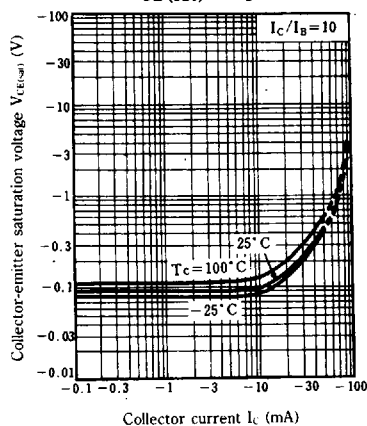
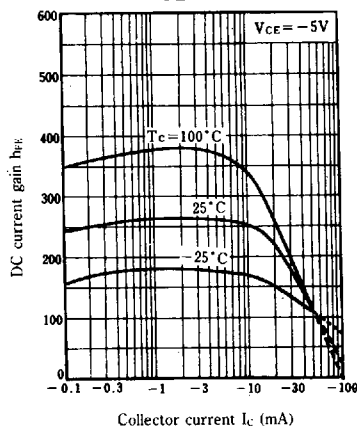
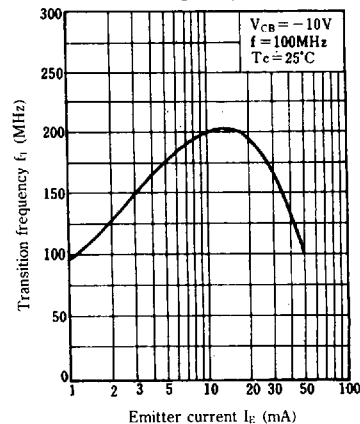
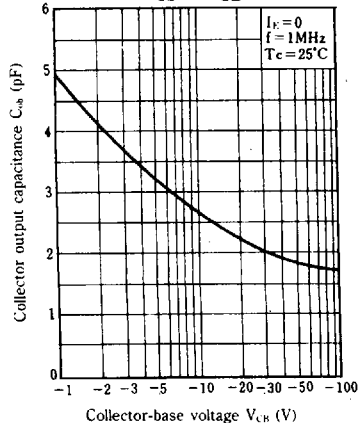


Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -100\text{ V}, I_E = 0$			-1	μA
Collector-emitter voltage	V_{CEO}	$I_C = -0.1\text{ mA}, I_B = 0$	-150			V
Emitter-base voltage	V_{EBO}	$I_E = -10\text{ }\mu\text{A}, I_C = 0$	-5			V
DC current gain	h_{FE}^*	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	90		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -30\text{ mA}, I_B = -3\text{ mA}$			-1	V
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 10\text{ mA}, f = 200\text{ MHz}$	70	200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$			5	pF

* h_{FE} Classifications

Class	Q	R	S	T
h_{FE}	90 ~ 155	130 ~ 220	185 ~ 330	260 ~ 450

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 

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